Ordering number:ENN6363

N-Channel Silicon MOSFET

5HN02C

Ultrahigh-Speed Switching Applications

Features

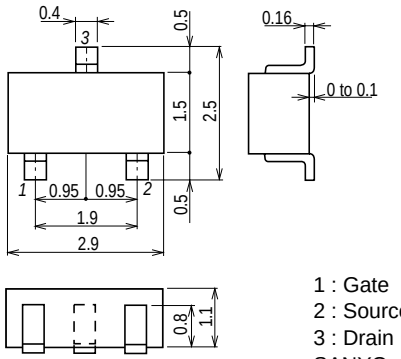
- Low ON resistance.
- Ultrahigh-speed switching.
- 4V drive.

Package Dimensions

unit:mm

2091A

[5HN02C]



1 : Gate
2 : Source
3 : Drain
SANYO : CP

Specifications

Absolute Maximum Ratings at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		50	V
Gate-to-Source Voltage	V_{GSS}		±20	V
Drain Current (DC)	I_D		0.2	A
Drain Current (pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	0.8	A
Allowable Power Dissipation	P_D		0.25	W
Channel Temperature	Tch		150	˚C
Storage Temperature	Tstg		–55 to +150	˚C

Electrical Characteristics at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA, V_{GS}=0	50			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=50V, V_{GS}=0			10	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±16V, V_{DS}=0			±10	μA
Cutoff Voltage	V_{GS}(off)	V_{DS}=10V, I_D=100μA	1		2.4	V
Forward Transfer Admittance	| yfs |	V_{DS}=10V, I_D=100mA	0.22	0.31		S
Static Drain-to-Source On-State Resistance	R_{DS}(on)1	I_D=100mA, V_{GS}=10V		1.8	2.3	Ω
	R_{DS}(on)2	I_D=50mA, V_{GS}=4V		2.3	3.2	Ω

Marking : YF

Continued on next page.

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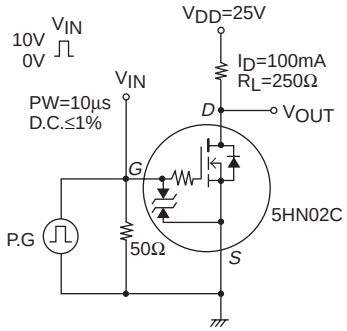
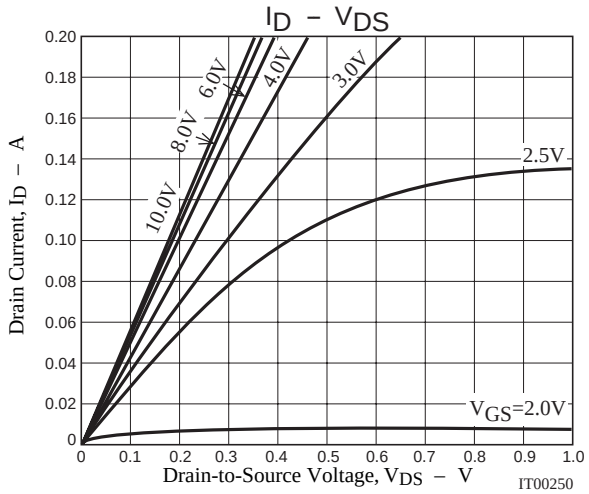
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

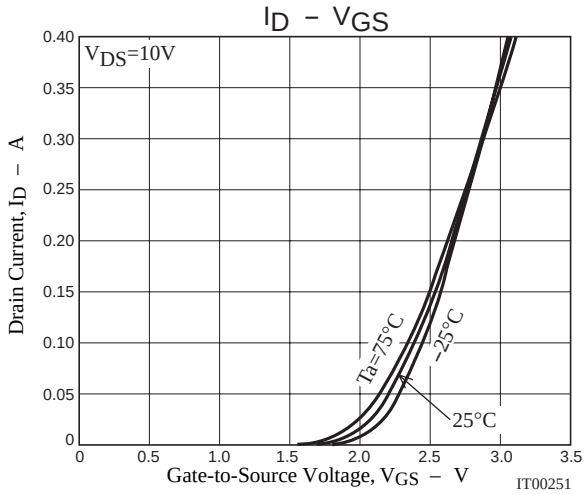
Continued from preceding page.

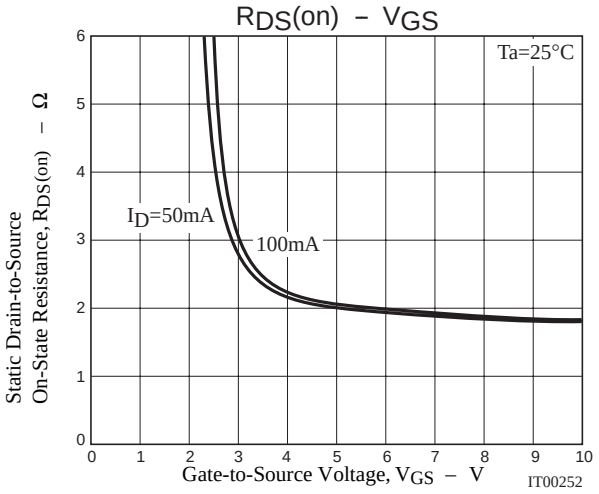
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	V_{DS}=10V, f=1MHz		22		pF
Output Capacitance	Coss	V_{DS}=10V, f=1MHz		12		pF
Reverse Transfer Capacitance	Crss	V_{DS}=10V, f=1MHz		4.6		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit		12		ns
Rise Time	t_r	See specified Test Circuit		12		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit		260		ns
Fall Time	t_f	See specified Test Circuit		110		ns
Total Gate Charge	Qg	V_{DS}=10V, V_{GS}=10V, I_D=200mA		1.86		nC
Gate-to-Source Charge	Qgs	V_{DS}=10V, V_{GS}=10V, I_D=200mA		0.28		nC
Gate-to-Drain "Miller" Charge	Qgd	V_{DS}=10V, V_{GS}=10V, I_D=200mA		0.45		nC
Diode Forward Voltage	V_{SD}	I_S=200mA, V_{GS}=0		0.83	1.2	V

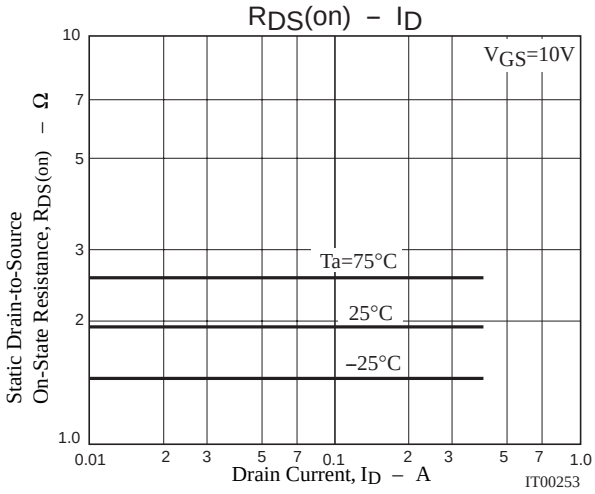
Switching Time Test Circuit

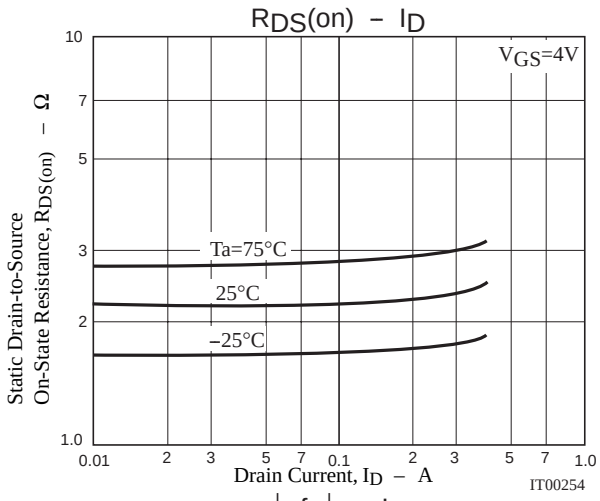


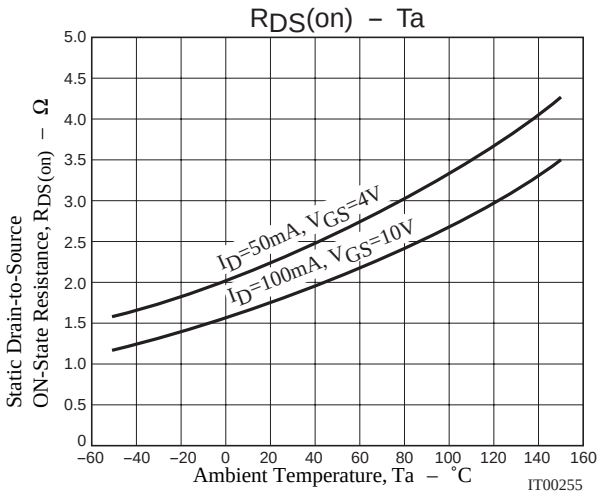


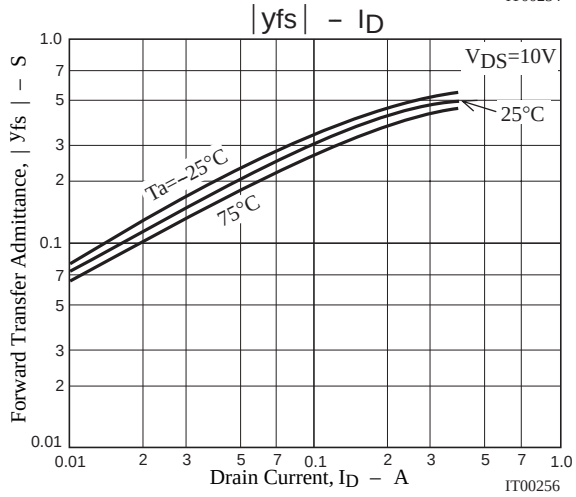


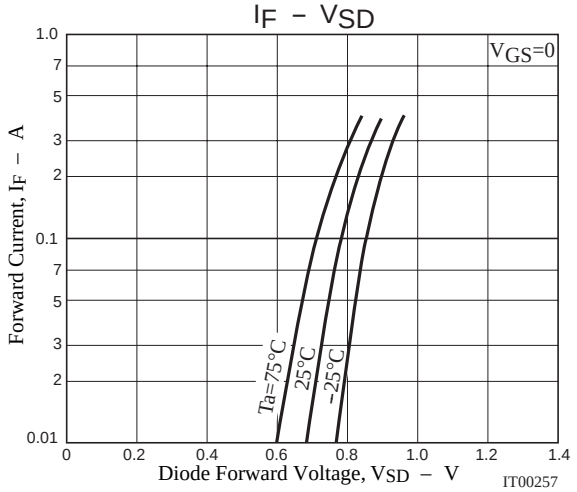


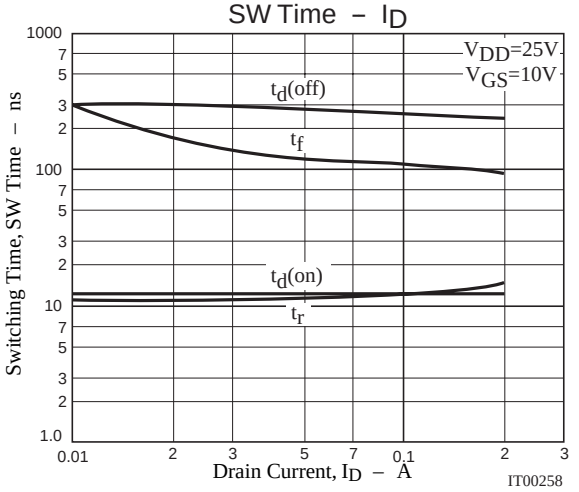


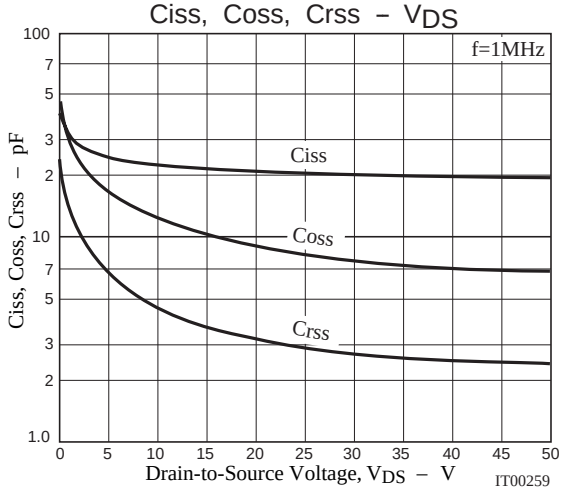

RDS(on) – ID
VGS=4V
Ta=75°C
25°C
–25°C
Static Drain-to-Source On-State Resistance, RDS(on) – Ω
Drain Current, ID – A
IT00254

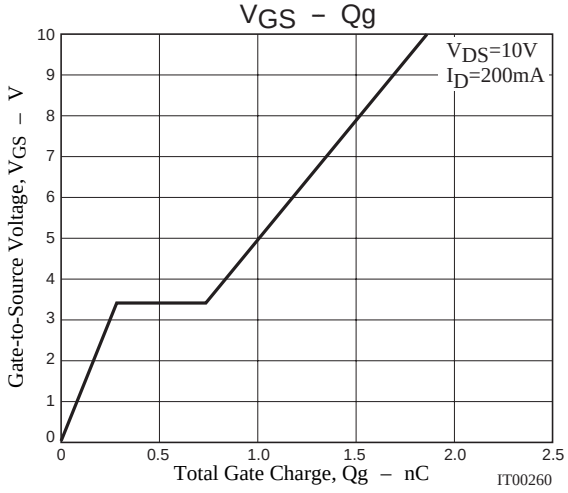

RDS(on) – Ta
ID=50mA, VGS=4V
ID=100mA, VGS=10V
Static Drain-to-Source ON-State Resistance, RDS(on) – Ω
Ambient Temperature, Ta – °C
IT00255

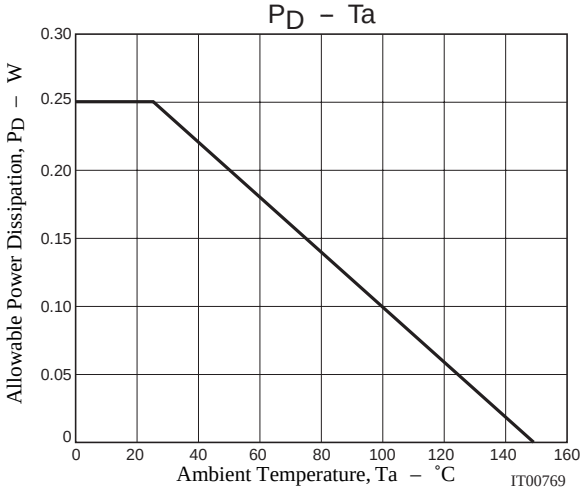

|yfs| – ID
VDS=10V
25°C
Ta=–25°C
75°C
Forward Transfer Admittance, |yfs| – S
Drain Current, ID – A
IT00256


IF – VSD
VGS=0
Ta=75°C
25°C
–25°C
Forward Current, IF – A
Diode Forward Voltage, VSD – V
IT00257


SW Time – ID
VDD=25V
VGS=10V
td(off)
tf
td(on)
tr
Switching Time, SW Time – ns
Drain Current, ID – A
IT00258


Ciss, Coss, Crss – VDS
f=1MHz
Ciss
Coss
Crss
Ciss, Coss, Crss – pF
Drain-to-Source Voltage, VDS – V
IT00259


VGS – Qg
VDS=10V
ID=200mA
Gate-to-Source Voltage, VGS – V
Total Gate Charge, Qg – nC
IT00260


PD – Ta
Allowable Power Dissipation, PD – W
Ambient Temperature, Ta – °C
IT00769